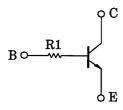
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

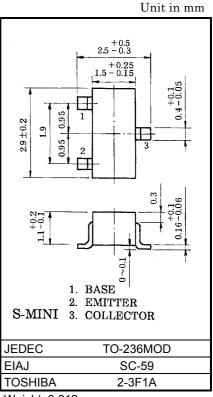
RN1441, RN1442, RN1443, RN1444

Muting And Switching Applications

- High emitter-base voltage: $V_{EBO} = 25V$ (min)
- High reverse hFE: reverse hFE = 150 (typ.) (VCE = -2V, IC = -4mA) •
- Low on resistance: $R_{ON} = 1\Omega$ (typ.) (IB = 5mA)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

Equivalent Circuit





Weight: 0.012g

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	50	V
Collector-emitter voltage	V _{CEO}	20	V
Emitter-base voltage	V _{EBO}	25	V
Collector current	Ι _C	300	mA
Collector power dissipation	P _C	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C

Marking

Type No.	H _{FE} classification			
	А	В		
RN1441	KA	KB		
RN1442	LA	LB		
RN1443	NA	NB		
RN1444	CA	СВ		

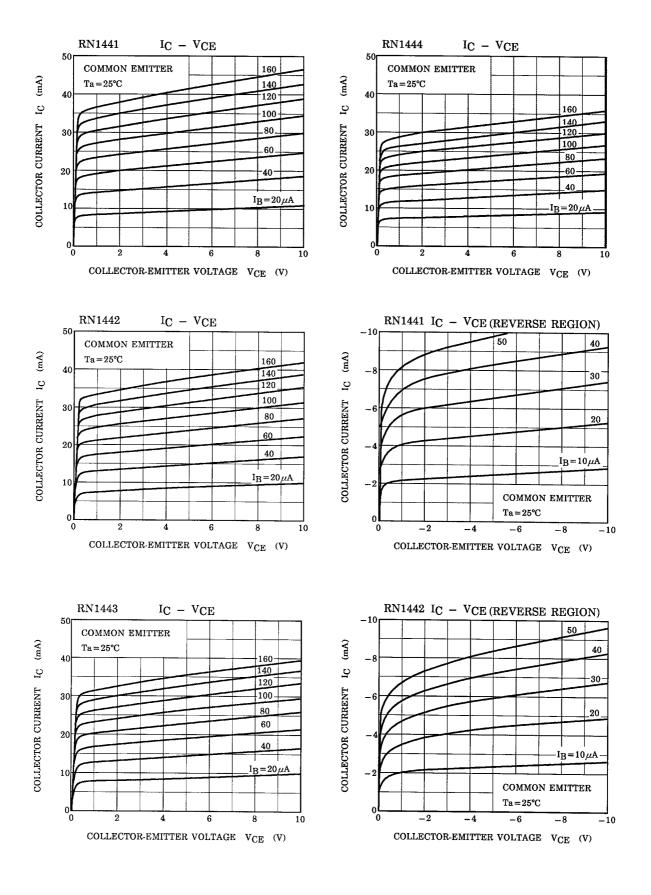
Electrical Characteristics (Ta = 25°C)

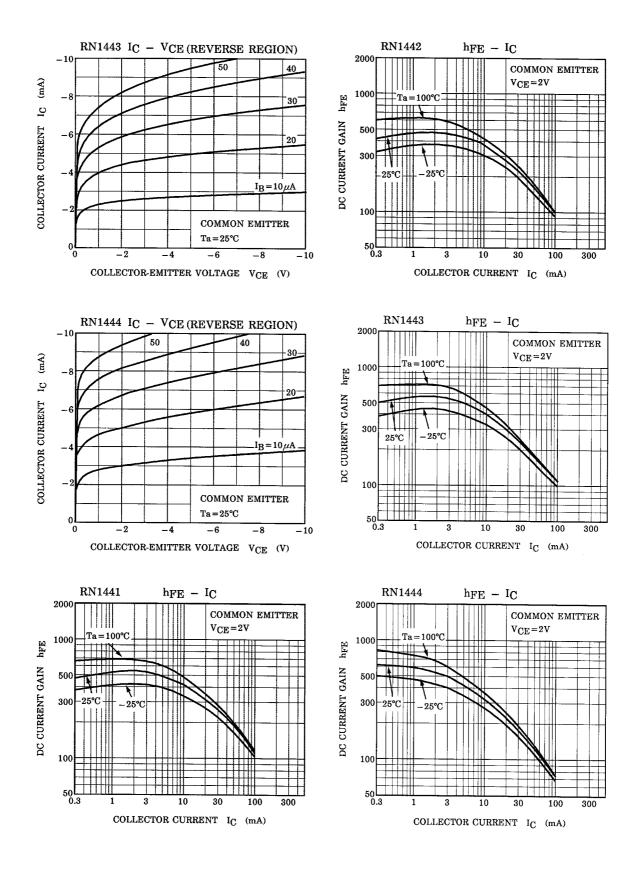
Characteris	tic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	_	$V_{CB} = 50V, I_E = 0$	_	_	0.1	μA
Emitter cut-off current		I _{EBO}	_	V _{EB} = 25V, I _C = 0	_	_	0.1	μA
DC current gain		h _{FE (Note)}	_	V_{CE} = 2V, I_C = 4mA	200	_	1200	
Collector-emitter saturation voltage		V _{CE (sat)}	_	I _C = 30mA, I _B = 3mA	_	_	0.1	V
Transition frequency		f _T	_	V_{CE} = 6V, I_C = 4mA	_	30	_	MHz
Collector output capacitance		C _{ob}	_	V _{CB} = 10V, I _E = 0, f = 1MHz	_	4.8	_	pF
Input resistor	RN1441	R1 –	_	_	3.9	5.6	7.3	kΩ
	RN1442				7	10	13	
	RN1443				15.4	22	28.6	
	RN1444					1.54	2.2	2.86

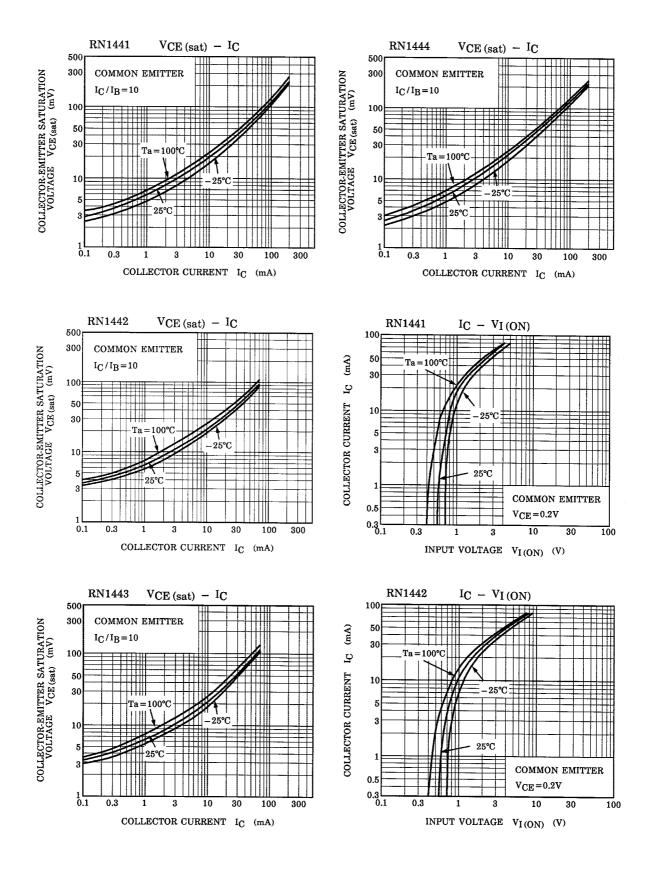
Note $: h_{\mathsf{FE}}$ classification

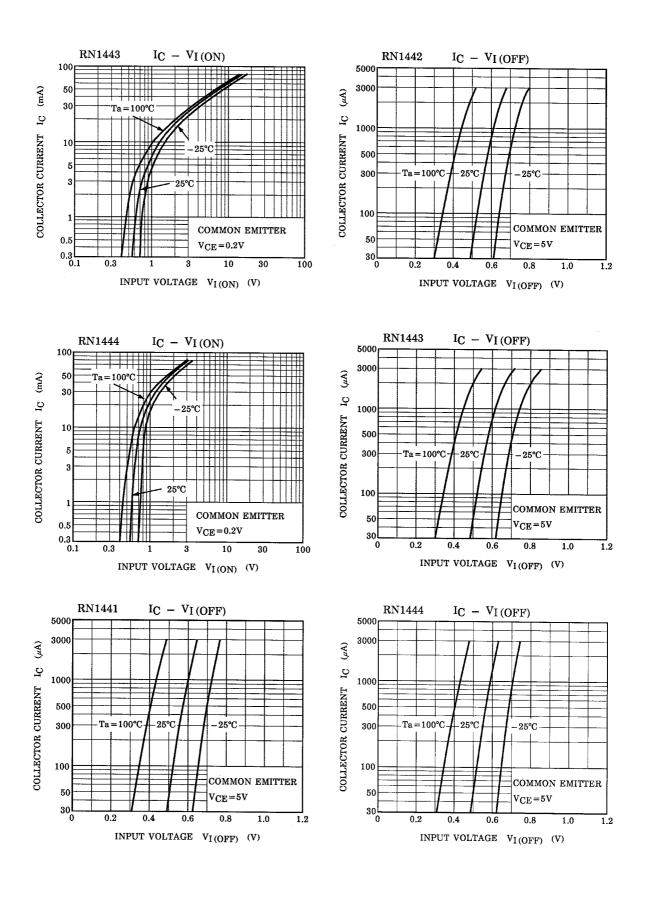
A: 200~700 B:

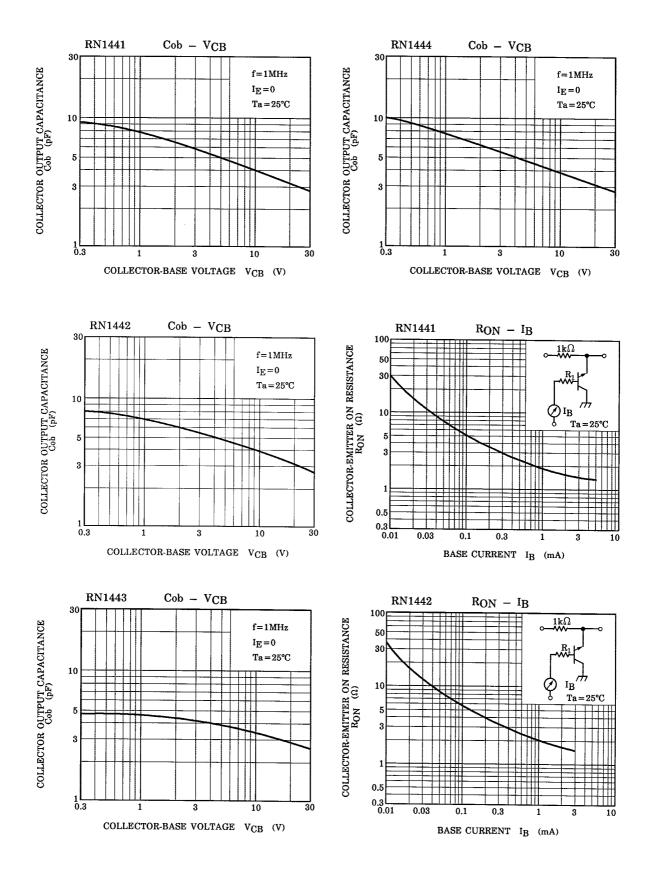
B: 350~1200

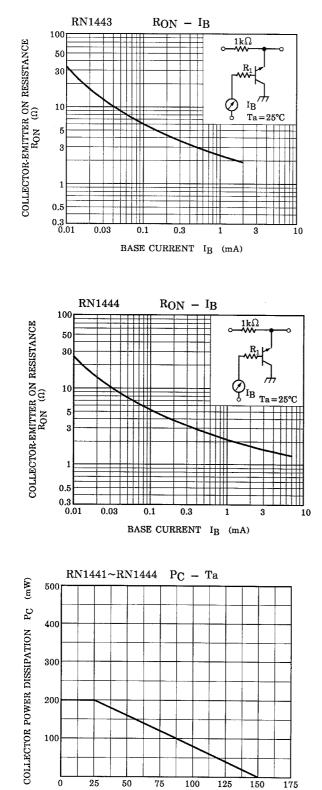












AMBIENT TEMPERATURE Ta (°C)

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